## **SIEMENS**

## **Data sheet**

6ES7648-2BF10-0XG0

SIMATIC CFast memory card, 4 GB, for IPCs with corresponding slot Further information, Quantity and content: see technical data



General information		
Product type designation	CFast memory card	
Supply voltage		
Type of supply voltage	DC	
Rated value (DC)	3.3 V; ±5 %	
Power		
Active power input, typ.	0.7 W; Inactive 0.3 W	
Memory		
Type of memory	CFast Type I	
Design	SLC NAND flash	
Memory size	4 Gbyte; 1 year (data retention)	
Speed class	Write speed: up to 60 MB/s (UDMA6), read speed: up to 100 MB/s (UDMA6)	
SLC flash write cycles	4.5; TB; number of write cycles determines the lifetime - with flash mass storage devices, the maximum number of possible write cycles is limited due to the physical properties of the flash cells. The intelligent data management of the flash controller ensures that the write cycle count of the mass storage device far surpasses the write cycles of a single flash memory cell. To ensure overall performance, it is recommended not use the memory area completely.	
Standards, approvals, certificates		
CE mark	Yes	
RoHS conformity	Yes	
Ambient conditions		
Ambient temperature during operation		
• min.	-40 °C; Any mounting angle	
• max.	85 °C; Any mounting angle	
Ambient temperature during storage/transportation		
• min.	-50 °C	
• max.	100 °C	
Relative humidity		
<ul> <li>Operation, max.</li> </ul>	85 %	
<ul> <li>Condensation permissible</li> </ul>	No	
Accessories		
Function description	fixed mode, multiple partitions possible	
Mechanics/material		
Enclosure material (front)		
• Plastic	Yes	
Dimensions		
Width	42.8 mm	

Height	36.4 mm
Thickness	3.6 mm
Weights	
Weight, approx.	10 g
Weight (without packaging)	10 g
Other	
Merchandise	No
Manufacturer name	SIEMENS AG
Manufacturer's address	Gleiwitzerstraße 555, 90475 Nuremberg, Germany
Target devices	For SIMATIC HMI devices and IPCs with the appropriate slot
Note:	bootable, real-time capable, error correction, wear leveling, power loss protection and diagnostics-capable

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